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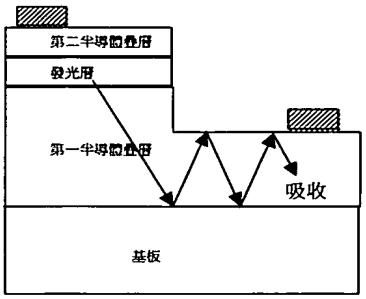
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發光層
第一半導體疊層
吸收
基板

圖 1A

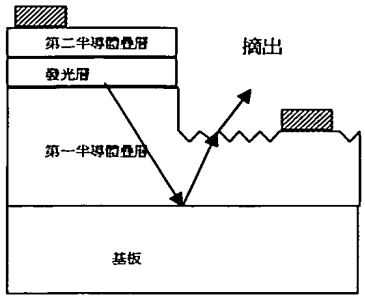
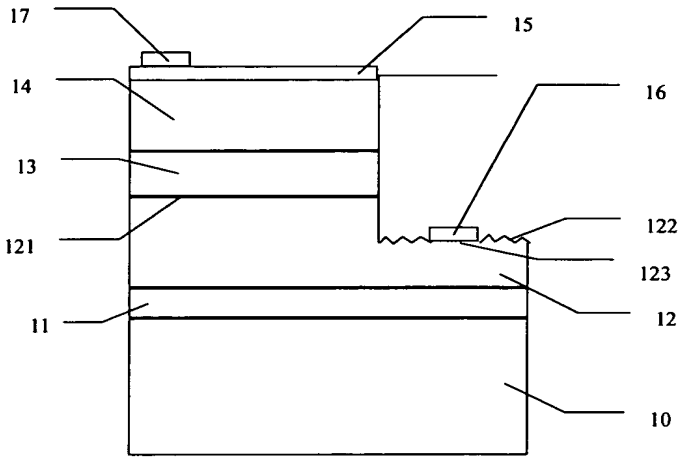

第二半導體疊層
摘出
發光層
第一半導體疊層
基板

圖 1B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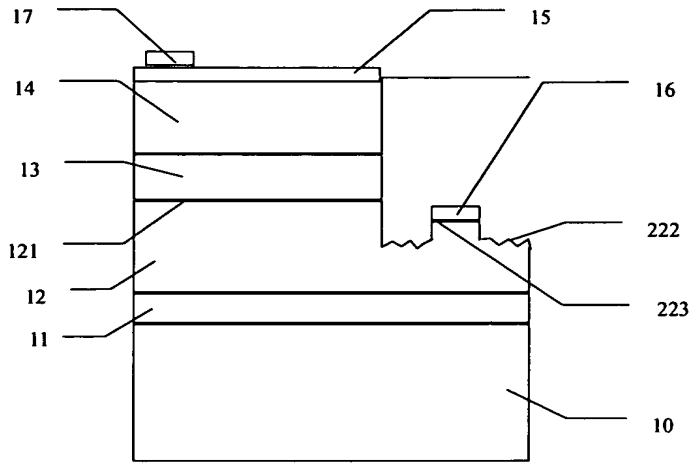
123
12
11
10

圖 2

圖式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222
121
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223
11
10

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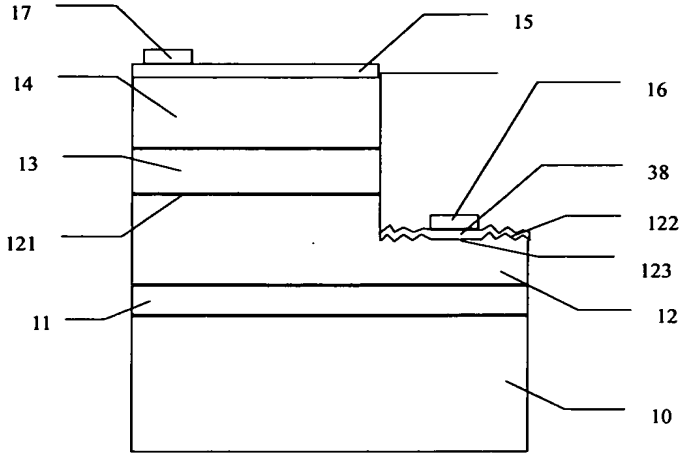
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圖 4

圖式

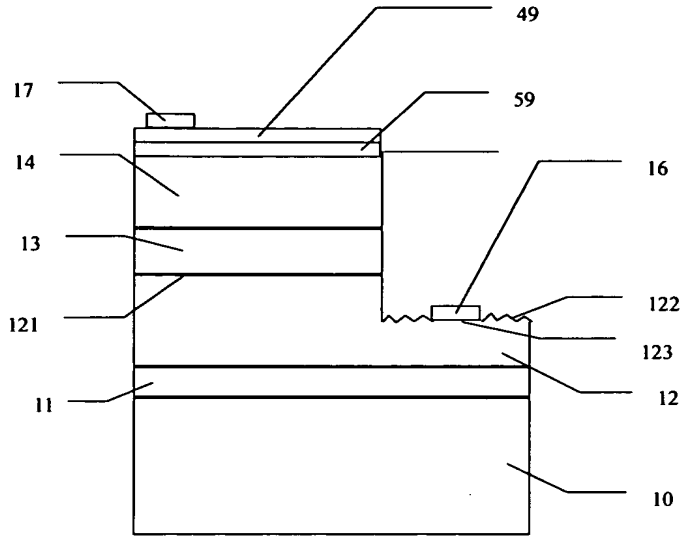
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圖 5

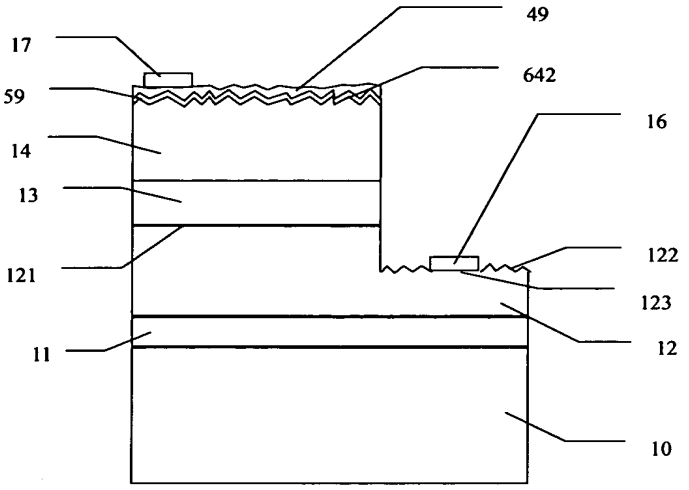
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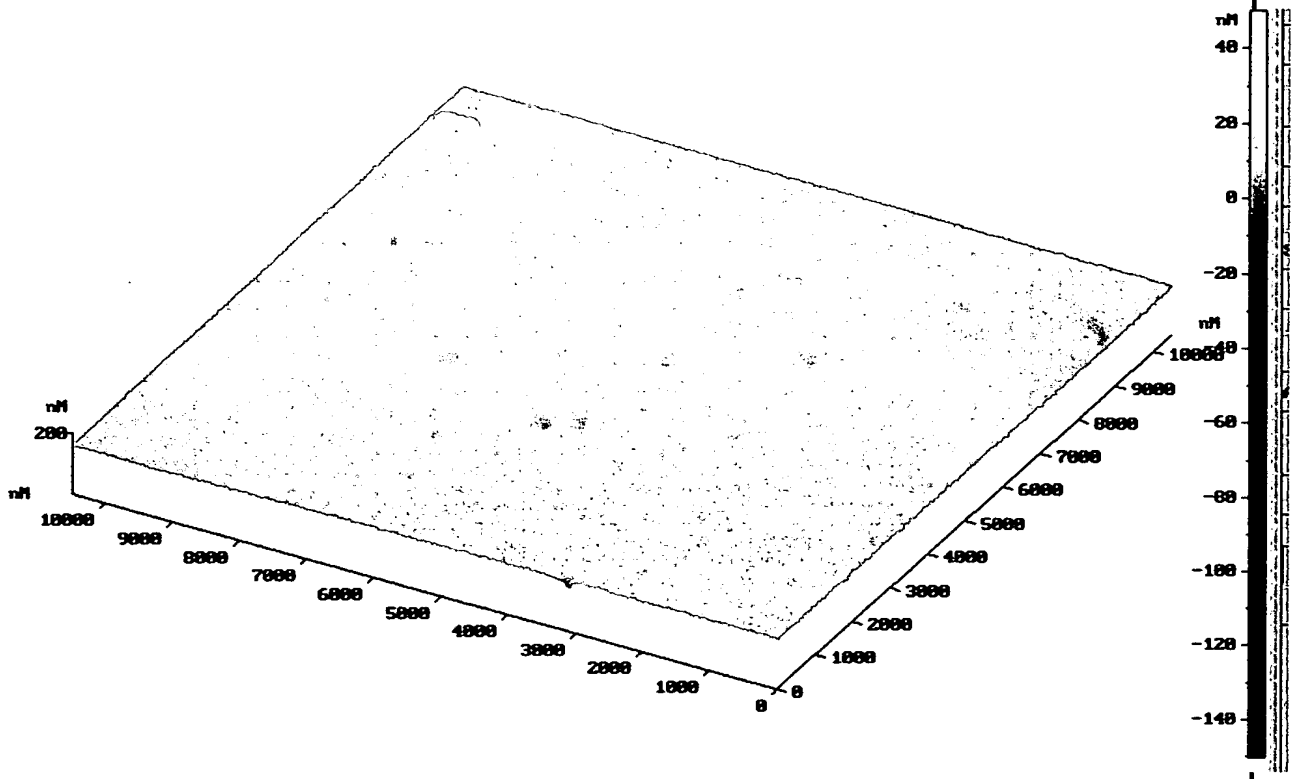
圖 6

圖式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nM
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7000
6000
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4000
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2000
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4000
5000
6000
7000
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9000
10000
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-20
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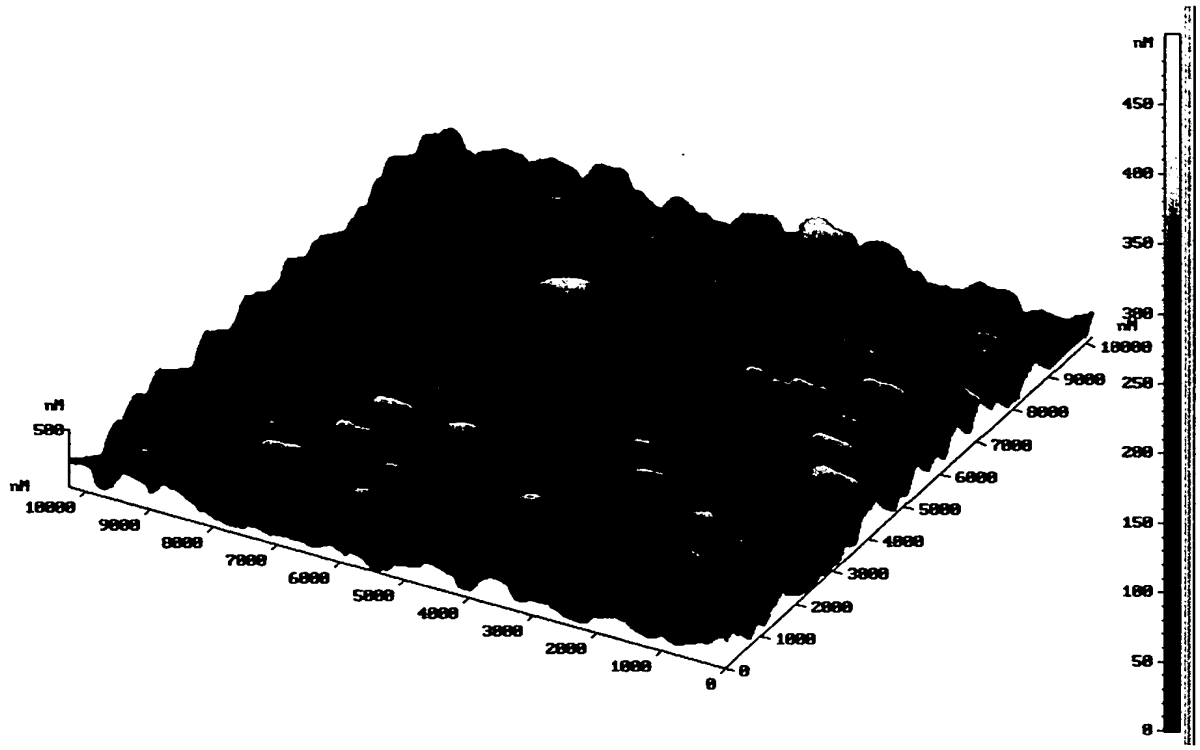
-40
-60
-80
-100
-120
-140

圖 7

圖式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300
250
200
150
100
50
0

圖 8

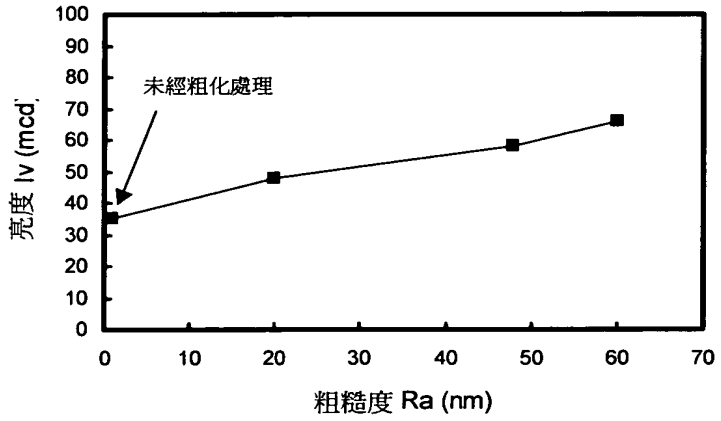
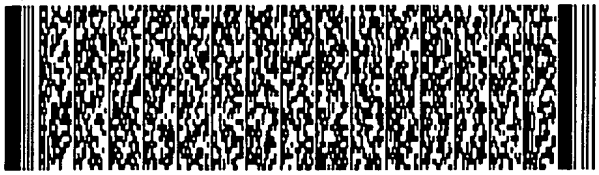

100
90
80
70
60
50
40
30
20
10
0
未經粗化處理
亮度 Iv (mcd)
0
10
20
30
40
50
60
70
粗糙度 Ra (nm)

圖 9

第 1/30 頁

第 2/30 頁

第 3/30 頁



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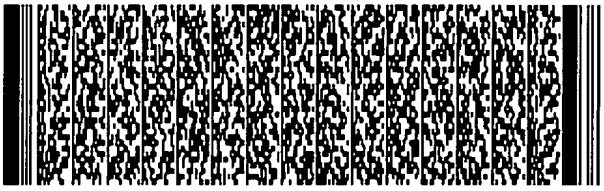
第 6/30 頁

第 7/30 頁



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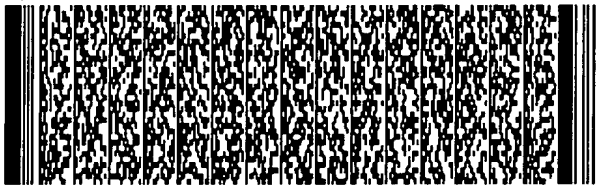

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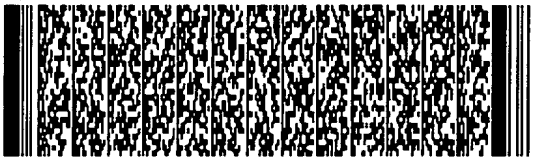

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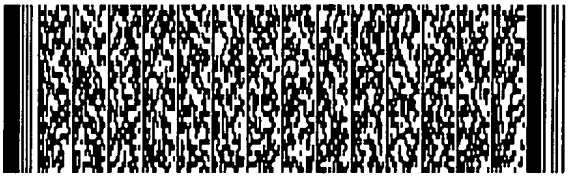
第 9/30 頁



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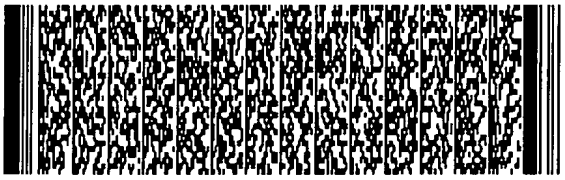

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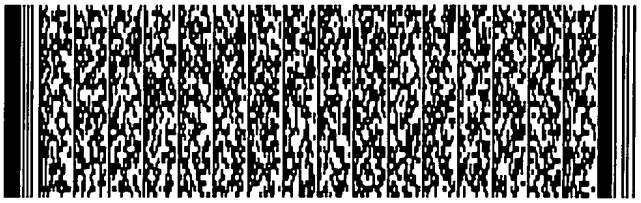

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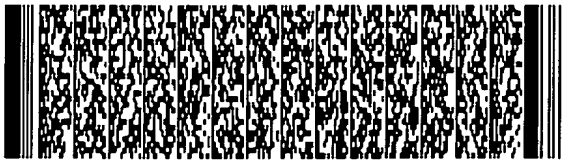

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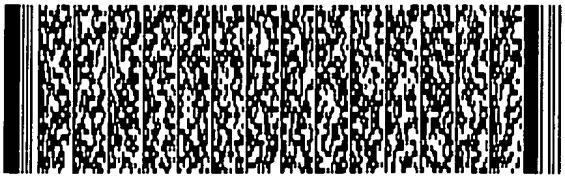
第 12/30 頁



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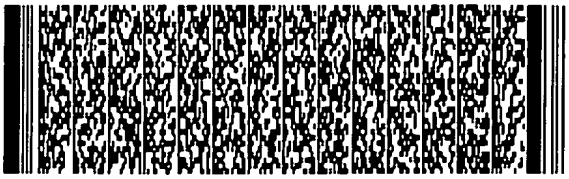

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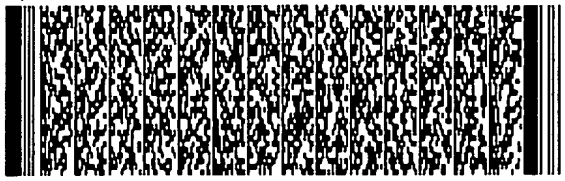

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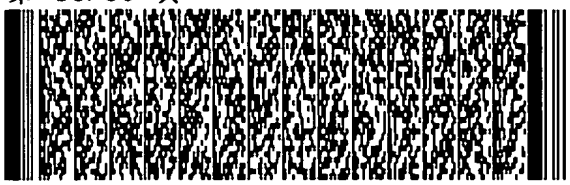

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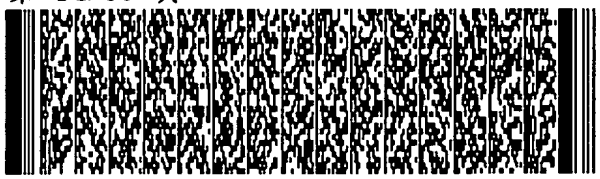

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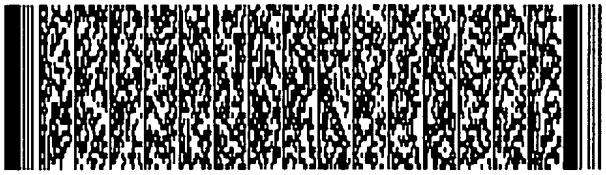

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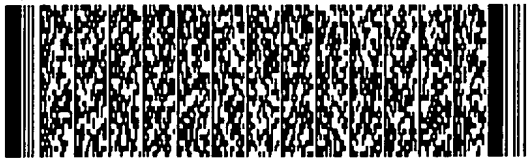

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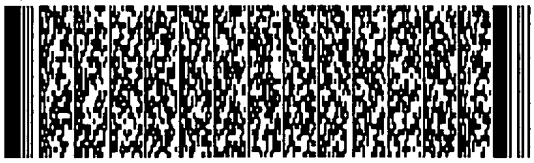

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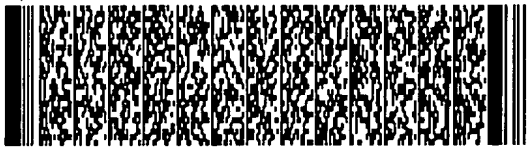

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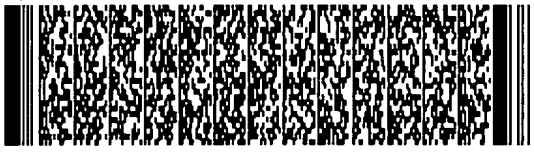

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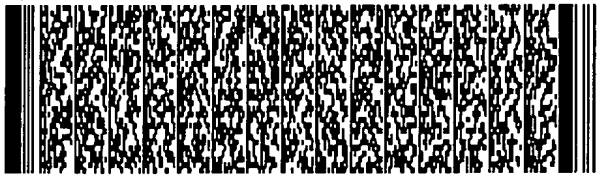

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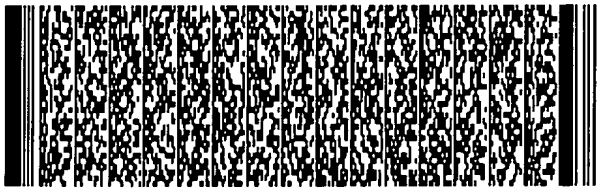
第 20/30 頁



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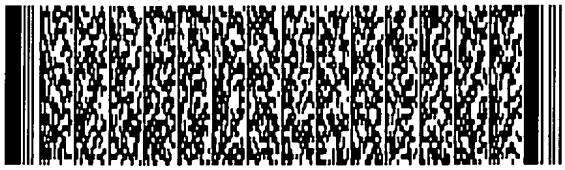
第 22/30 頁



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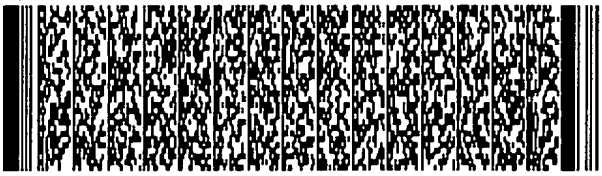

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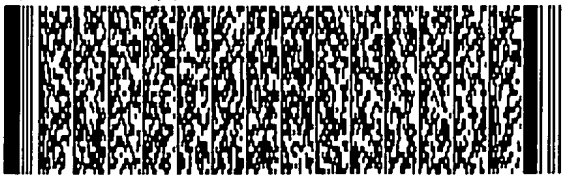

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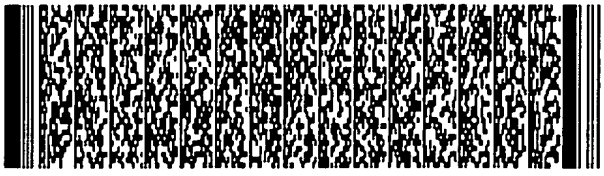

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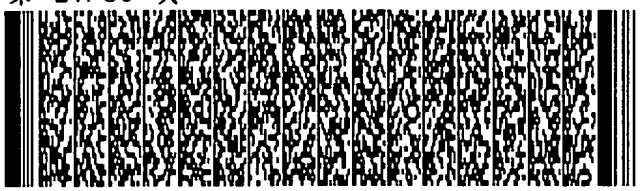
第 27/30 頁



第 28/30 頁

第 29/30 頁

第 30/30 頁